ABSTRACT

A polishing composition of the present invention, which is used in polishing the edge of a wafer for semiconductor devices, effectively suppresses remaining amounts of abrasives on the wafer. The polishing composition includes silicon dioxide, an alkaline compound, a water-soluble polymer, and water. The average primary particle diameter D_{SA} of the silicon dioxide is at least 40 nm. The ratio D_{95}/D_5 of the silicon dioxide is no more than 3.8. The value $D_{95}/D_5/D_{SA}$ of the silicon dioxide is no more than 0.07.